

ZXTP25100BFH 100V, SOT23, PNP medium power transistor

Summary

 $BV_{(BR)CEX} > -140V$, $BV_{(BR)CEO} > -100V$

 $BV_{(BR)ECX} > -7V$;

 $I_{C(cont)} = -2A$

V_{CE(sat)} < -130mV @ -1A

 $R_{CE(sat)} = 108m\Omega \text{ typical}$

 $P_{D} = 1.25W$

Complementary part number ZXTN25100BFH

Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

Features

- · High power dissipation SOT23 package
- · High peak current
- · Low saturation voltage
- · 140V forward blocking voltaget
- 7V reverse blocking voltage

Applications

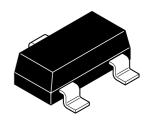
- · MOSFET and IGBT gate driving
- · DC DC converters
- · Motor drive
- · Relay, lamp, and solenoid drive

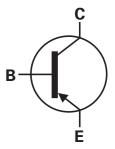
Ordering information

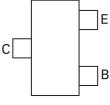
Device	Device Reel size (inches)		Quantity per reel	
ZXTP25100BFHTA	7	8mm	3,000	

Device marking

056







Pinout - top view

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V _{CBO}	-140	V
Collector-emitter voltage (forward blocking)	V _{CEX}	-140	V
Collector-emitter voltage	V _{CEO}	-100	V
Emitter-collector voltage (reverse blocking)	V _{ECX}	-7	V
Emitter-base voltage	V _{EBO}	-7	V
Continuous collector current (b)	I _C	-2	Α
Peak pulse current	I _{CM}	-5	Α
Power dissipation at T _A =25°C ^(a) Linear derating factor	P _D	0.73 5.84	W mW/°C
Power dissipation at T _A =25°C ^(b) Linear derating factor	P _D	1.05 8.4	W mW/°C
Power dissipation at T _A =25°C ^(c) Linear derating factor	P _D	1.25 9.6	W mW/°C
Power dissipation at T _A =25°C ^(d) Linear derating factor	P _D	1.81 14.5	W mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	171	°C/W
Junction to ambient ^(b)	$R_{\Theta JA}$	119	°C/W
Junction to ambient ^(c)	$R_{\Theta JA}$	100	°C/W
Junction to ambient ^(d)	$R_{\Theta JA}$	69	°C/W

NOTES:

⁽a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

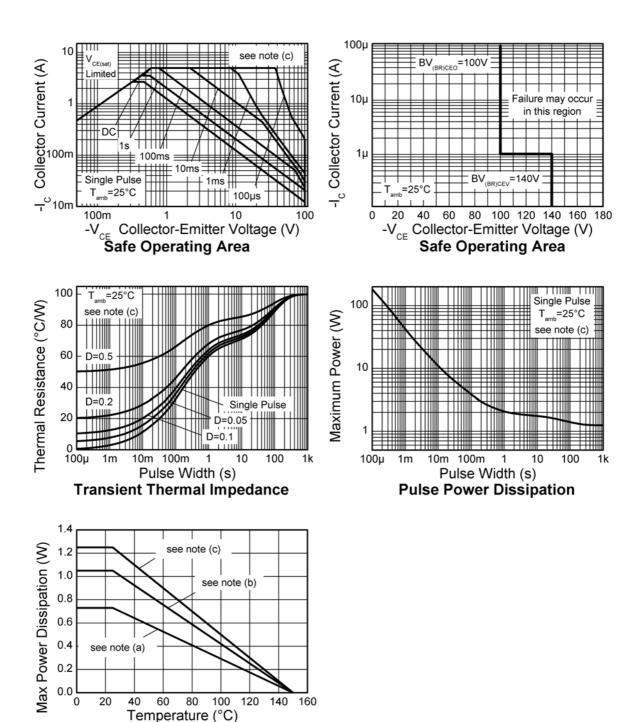
⁽b) Mounted on 25mm \times 25mm \times 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

⁽c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

⁽d) As (c) above measured at t<5secs.

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Characteristics



Derating Curve

Electrical characteristics (at $T_{AMB} = 25^{\circ}C$ unless otherwise stated)

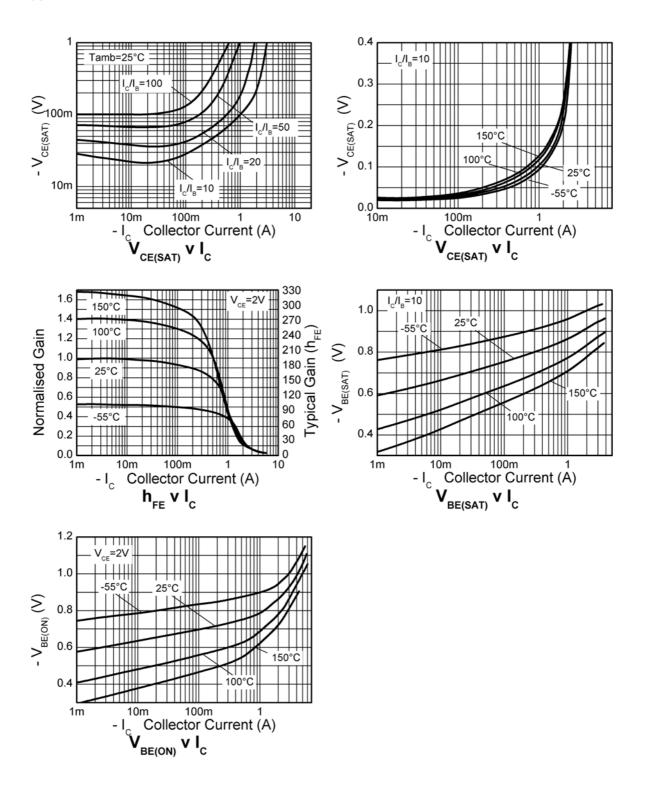
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	-140	-165		V	$I_C = -100 \mu A$
Collector-emitter breakdown voltage (forward blocking)	BV _{CEX}	-140	-165		V	I_C = -100μA, R_{BE} < 1k Ω or -0.25V < V_{BE} < 1V
Collector-emitter breakdown voltage (base open)	BV _{CEO}	-100	-125		V	I _C = -10mA ^(*)
Emitter-collector breakdown voltage (reverse blocking)	BV _{ECX}	-7	8.2		V	$\begin{split} I_E &= -100 \mu A, \\ R_{BC} &< 1 k \Omega \text{ or} \\ -0.25 V &< V_{BC} < 0.25 V \end{split}$
Emitter-base breakdown voltage	BV _{EBO}	-7	-8.2		V	I _E = -100μA
Collector cut-off current	I _{CBO}		<-1	-50 -20	nA μA	V _{CB} = -112V V _{CB} = -112V, T _{AMB} = 100°C
Collector emitter cut-off current	I _{CEX}		-	-100	nA	$V_{CE} = -112V;$ $R_{BE} < 1k\Omega \text{ or}$ $-0.25V < V_{BE} < 1V$
Emitter cut-off current	I _{EBO}		<-1	-50	nA	V _{EB} = -5.6V
Collector-emitter	V _{CE(sat)}		-60	-90	mV	$I_C = -0.5A$, $I_B = -50mA$ (*)
saturation voltage			-240	-350	mV	I _C = -0.5A, I _B = -10mA ^(*)
			-100	-130	mV	I _C = -1A, I _B = -100mA ^(*)
			-215	-295	mV	I _C = -2A, I _B = -200mA ^(*)
Base-emitter saturation voltage	V _{BE(sat)}		-900	-1000	mV	I _C = -2A, I _B = -200mA ^(*)
Base-emitter turn-on voltage	V _{BE(on)}		-830	-950	mV	$I_C = -2A$, $V_{CE} = -2V^{(*)}$
Static forward current	h _{FE}	100	200	300		$I_C = -10 \text{mA}, V_{CE} = -2V^{(*)}$
transfer ratio		55	105			$I_C = -1A$, $V_{CE} = -2V^{(*)}$
		15	25			$I_C = -2A$, $V_{CE} = -2V^{(*)}$
Transition frequency	f _T		200		MHz	I _C = -100mA, V _{CE} = -5V f = 100MHz
Output capacitance	C _{OBO}		15	25	pF	V _{CB} = -10V, f = 1MHz ^(*)
Turn-on time	t _(on)		31		ns	$V_{CC} = -10V, I_{C} = -500mA,$
Turn-off time	t _(off)		384		ns	$I_{B1} = I_{B2} = -50 \text{mA}$

NOTES:

^(*) Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%.

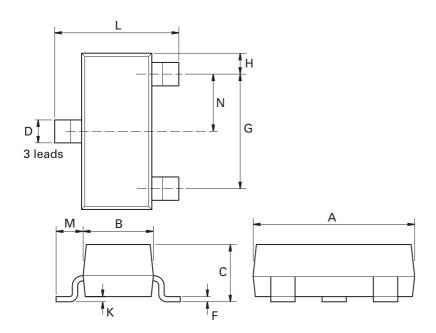
ZXTP25100BFH

Typical characteristics



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Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
Α	2.67	3.05	0.105	0.120	Н	0.33	0.51	0.013	0.020
В	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
С	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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